



For/\$

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

**INFORMATION DISCLOSURE STATEMENT**

APPLICANT(S): Dharam Pal Gosain

DOCKET NO.: 09792909-5657

SERIAL NO.: 10/645,805

GROUP ART UNIT: 2813

DATE FILED: August 21, 2003

EXAMINER: Laura M. Schillinger

INVENTION: METHOD OF PRODUCING CRYSTALLINE SEMICONDUCTOR  
MATERIAL AND METHOD OF FABRICATING SEMICONDUCTOR DEVICE

Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

S I R:

In accordance with the provisions of 37 C.F.R. § 1.56, Applicants request that citation and examination of the references identified on the attached PTO-1449 form, in accordance with 37 C.F.R. §1.98, be made during the course of examination of the above-referenced application for United States Letters Patent.

These listed items were cited in a Search Report issued as current with Singapore Application #200304828-7 on June 29, 2005. A copy of the Search Report also is enclosed.

Respectfully submitted by,

(Reg. 54,218)

W. John Keyes  
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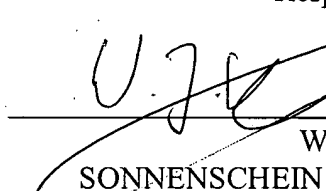
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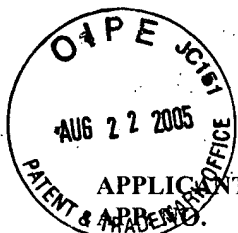
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APPLICANT:  
APPENDIX:  
FILING DATE:  
INVENTION:

Dharam Pal Gosain  
10/645/805  
August 21, 2003

ATTORNEY DOCKET NO. 09792909-5657  
GROUP ART UNIT: 2813

EXAMINER: Laura M. Schillinger  
"METHOD OF PRODUCING CRYSTALLINE SEMICONDUCTOR MATERIAL AND METHOD  
OF FABRICATING SEMICONDUCTOR DEVICE"

INFORMATION DISCLOSURE STATEMENT TRANSMITTAL LETTER

Commissioner of Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Submitted herewith is a Supplemental Information Disclosure Statement for consideration in the above-identified application. This Supplemental Information Disclosure Statement is submitted:

- ☐ Within 3 months (1) of filing date of a national application; (2) of date of entry of the national stage as set forth in 37 C.F.R. §1.491 in an international application; or (3) before the mailing date of a first Office Action on the merits, whichever occurs last. (No fee is required.)
- ☒ After the mailing date of a first Office Action but before (1) mailing of a final action under 37 C.F.R. §1.113; or (2) mailing of a notice of allowance under §1.311, whichever occurs first.
- ☒ Payment for the fee set forth in 37 C.F.R. §1.17(p) accompanies this submission; or
- ☐ The certification specified in 37 C.F.R. §1.97(e) is made below. (No fee is required.)
- ☐ After the mailing of (1) a final action under 37 C.F.R. §1.113; or (2) a notice of allowance under 37 C.F.R. §1.311 whichever occurs first, but **before** payment of the issue fee. The certification specified in 37 C.F.R. §1.97(e) is made below. The Commissioner hereby is petitioned to consider the Information Disclosure Statement accompanying this submission. Payment for the Petition fee set forth in 37 C.F.R. §1.17(i)(1) accompanies this submission.
- ☒ The undersigned counsel for applicant(s) hereby certifies each item of information contained in the Information Disclosure Statement was cited in a communication from a foreign Patent Office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement.
- ☐ The undersigned counsel for applicant(s) hereby certifies that no item of information contained in the Information Disclosure Statement was first cited in a communication from a foreign Patent Office in a counterpart foreign application, or to the knowledge of the undersigned, after making reasonable inquiry, was known to any individual designated in 37 C.F.R. §1.56(c) more than three months prior to the filing of this Information Disclosure Statement.
- ☒ The Commissioner is hereby authorized to charge any additional fees which may be required, or credit any overpayment to Account No. 19-3140. *A duplicate copy of this sheet is enclosed for this purpose.*

Very respectfully,

When phoning re this application,  
please call (312) 876-8000

W. John Keyes, Ph.D., Reg. 54,218  
Sonnenschein, Nath & Rosenthal LLP  
P.O. Box 061080  
Wacker Drive Station, Sears Tower  
Chicago, Illinois 60606  
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**CERTIFICATE OF MAILING**

I hereby certify that this Information Disclosure Statement is being deposited with the United States Postal Service in an envelope addressed to the Commissioner for Patents at the United States Patent and Trademark Office, P. O. Box 1450, Alexandria, VA 22313-1450 via First-Class Mail on August 17, 2005.

W. John Keyes

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT:  
APP. NO.  
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INVENTION:

Dharam Pal Gosain  
10/645/805  
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W. John Keyes

37 CFR 1.501 INFORMATION DISCLOSURE STATEMENT IN A PATENT (use several sheets if necessary)						Docket No. 09792909-5657		Serial No. 10/645,805	
				Applicants: Dharam Pal Gosain					
				Filing Date August 21, 2003		Group Art Unit 2813			

U.S. PATENT DOCUMENTS							
Examiner's Initials		Document Number	Date	Country	Class	Subclass	Filing Date If appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						

FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AH							
	AI							
	AJ							
	AK							
	AL							
	AM							
	AN							
	AO							
	AP							
	AQ							
	AR							
	AS							
	AT							

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
	AU	Australian Search Report
	AV	Derwent Abstract Accession No. 89-351354/48, Class U11, JP 01-261291 A (Agency of Ind Sci Tech) 18 October 1989 Abstract (Relevant to Claim No. 1-37).
	AW	SMITH et al, 'Silicon-on-insulator by graphoepitaxy and zone-melting recrystallization of patterned films', Journal of Crystal Growth, North-Holland, 1983, vol. 73, pages 527-546 Section 3 (Relevant to Claim No. 1-37).
	AX	ISHIHARA, R.K., 'Location control of laterally columnar Si grains by dual-beam excimer-laser melting of Si thin-film', Materials Research Society Symposium Proceedings, 2000, vol. 621, pages Q9.4.1-Q9.4.6. Whole document (Relevant to Claim No. 1-37).
	AY	

Examiner	Date Considered
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**\*EXAMINER:** Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.